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Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

- 1. (Original) A light emitting device comprising:
- a light emitting element provided in a pixel;
- a first transistor provided in said pixel for determining a current value flowing in the light emitting element; and
- a second transistor provided in said pixel for determining a light emission or nonemission of the light emitting element according to a video signal,

wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

- a gate electrode of the first transistor is connected to the first power supply; and the first transistor is a depletion mode transistor.
- 2. (Currently Amended) [[A]] <u>The</u> device according to claim 1, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 3. (Currently Amended) [[A]] <u>The</u> device according to claim 1, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 4. (Currently Amended) [[A]] <u>The</u> device according to claim 1, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
 - 5. (Currently Amended) [[A]] The device according to claim 4, a ratio of the channel

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length to the channel width of the first transistor is five or more.

6. (Original) A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element; and

a second transistor provided in said pixel for determining a light emission or nonemission of the light emitting element according to a video signal,

wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and

- 7. (Currently Amended) [[A]] <u>The</u> device according to claim 6, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 8. (Currently Amended) [[A]] <u>The</u> device according to claim 6, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 9. (Currently Amended) [[A]] <u>The</u> device according to claim 6, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
- 10. (Currently Amended) [[A]] <u>The</u> device according to claim 9, a ratio of the channel length to the channel width of the first transistor is five or more.

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11. (Original) A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element; and

a second transistor provided in said pixel for determining a light emission or nonemission of the light emitting element according to a video signal; and

a third transistor provided in said pixel for controlling input of said video signal,

wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to the first power supply; and the first transistor is a depletion mode transistor.

- 12. (Currently Amended) [[A]] <u>The</u> device according to claim 11, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 13. (Currently Amended) [[A]] <u>The</u> device according to claim 11, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 14. (Currently Amended) [[A]] <u>The</u> device according to claim 11, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
- 15. (Currently Amended) [[A]] <u>The</u> device according to claim 14, a ratio of the channel length to the channel width of the first transistor is five or more.

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16. (Original) A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element;

a second transistor provided in said pixel for determining a light emission or nonemission of the light emitting element according to a video signal; and

a third transistor provided in said pixel for controlling input of said video signal,

wherein

the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and

- 17. (Currently Amended) [[A]] <u>The</u> device according to claim 16, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 18. (Currently Amended) [[A]] <u>The</u> device according to claim 16, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 19. (Currently Amended) [[A]] <u>The</u> device according to claim 16, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
- 20. (Currently Amended) [[A]] <u>The</u> device according to claim 19, a ratio of the channel length to the channel width of the first transistor is five or more.

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21. (Original) A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element;

- a second transistor provided in said pixel for determining a light emission or nonemission of the light emitting element according to a video signal;
 - a third transistor provided in said pixel for controlling an input of the video signal; and
- a fourth transistor provided in said pixel for setting the light emitting element in a nonemission state regardless of the video signal,

wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to the first power supply; and the first transistor is a depletion mode transistor.

- 22. (Currently Amended) [[A]] <u>The</u> device according to claim 21, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 23. (Currently Amended) [[A]] <u>The</u> device according to claim 21, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 24. (Currently Amended) [[A]] <u>The</u> device according to claim 21, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
 - 25. (Currently Amended) [[A]] The device according to claim 24, a ratio of the channel

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length to the channel width of the first transistor is five or more.

26. (Original) A light emitting device comprising a pixel comprising:

- a light emitting element provided in a pixel;
- a first transistor provided in said pixel for determining a current value flowing in the light emitting element;
- a second transistor provided in said pixel for determining a light emission or nonemission of the light emitting element according to a video signal;
 - a third transistor provided in said pixel for controlling an input of the video signal; and
- a fourth transistor provided in said pixel for setting the light emitting element in a nonemission state regardless of the video signal,

wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and

- 27. (Currently Amended) [[A]] <u>The</u> device according to claim 26, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 28. (Currently Amended) [[A]] <u>The</u> device according to claim 26, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 29. (Currently Amended) [[A]] <u>The</u> device according to claim 26, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.

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30. (Currently Amended) [[A]] <u>The</u> device according to claim 29, a ratio of the channel length to the channel width of the first transistor is five or more.

31. (Original) An element substrate comprising:

a pixel electrode provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the pixel electrode; and

a second transistor provided in said pixel for determining a current supply or no current supply to the pixel electrode according to a video signal,

wherein the first transistor is connected in series to the second transistor between a first power supply and the pixel electrode;

a gate electrode of the first transistor is connected to the first power supply; and the first transistor is a depletion mode transistor.

- 32. (Currently Amended) [[A]] <u>The</u> substrate according to claim 31, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 33. (Currently Amended) [[A]] <u>The</u> substrate according to claim 31, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 34. (Currently Amended) [[A]] <u>The</u> substrate according to claim 31, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
 - 35. (Currently Amended) [[A]] The substrate according to claim 34, wherein a ratio of the

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channel length to the channel width of the first transistor is five or more.

36. (Original) An element substrate comprising:

a pixel electrode provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the pixel electrode; and

a second transistor provided in said pixel for determining a current supply or no current supply to the pixel electrode according to a video signal,

wherein the first transistor is connected in series to the second transistor between a first power supply and the pixel electrode;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and

- 37. (Currently Amended) [[A]] <u>The</u> substrate according to claim 36, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.
- 38. (Currently Amended) [[A]] <u>The</u> substrate according to claim 36, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.
- 39. (Currently Amended) [[A]] <u>The</u> substrate according to claim 36, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.
- 40. (Currently Amended) [[A]] <u>The</u> substrate according to claim 39, wherein a ratio of the channel length to the channel width of the first transistor is five or more.